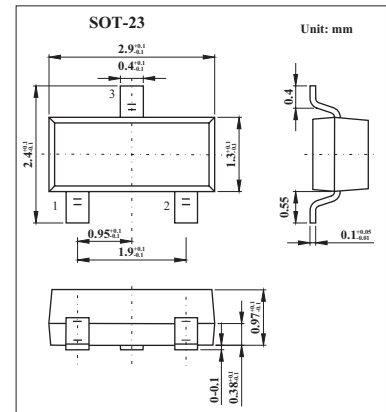


Silicon Epitaxial Planar Diode

HSM2692

■ Features

- Low forward resistance. ($r_f = 0.9 \text{ max}$)
- Low capacitance. ($C = 1.2 \text{ pFmax}$)
- MPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Power dissipation	P_d	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-45 to +125	$^\circ\text{C}$
Operation temperature	T_{opr}	-20 to +60	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse voltage	V_R	$I_R = 10 \mu\text{A}$	35			V
Reverse current	I_R	$V_R = 25 \text{ V}$			50	nA
Forward voltage	V_F	$I_F = 10 \text{ mA}$			1.0	V
Capacitance	C	$V_R = 6 \text{ V}, f = 1 \text{ MHz}$			1.2	pF
Forward resistance	r_f	$I_F = 2 \text{ mA}, f = 100 \text{ MHz}$			0.9	Ω

■ Marking

Marking	B1
---------	----